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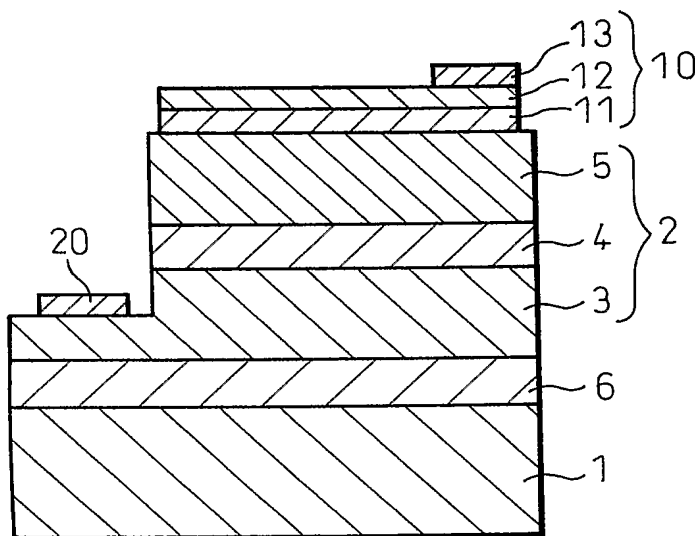
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(54) Title: TRANSPARENT POSITIVE ELECTRODE



(57) Abstract: An object of the present invention is to provide a positive electrode having high transparency, low contact resistance and excellent current diffusibility and not requiring electron beam irradiation, high-temperature annealing or heat treatment, for alloying, in an oxygen atmosphere. The inventive transparent positive electrode for gallium nitride-based compound semiconductor light-emitting devices comprises a contact metal layer in contact with a p-type semiconductor layer, a current diffusing layer on the contact metal layer, the current diffusing layer having an electrical conductivity larger than that of the contact metal layer.

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